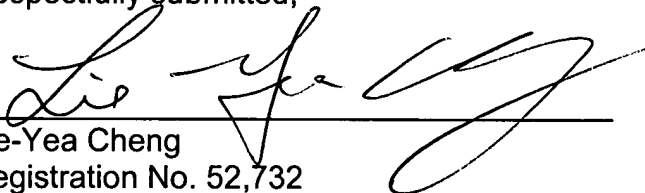


The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicants certify that all references submitted with this disclosure were cited in a communication from a foreign patent office dated October 23, 2003, which communication is enclosed, not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

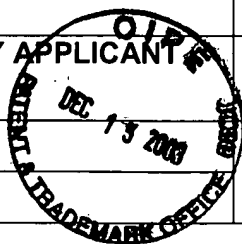
If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No.: 20-0782/AMAT/6437/LYC.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Lie-Yea Cheng", is written over a horizontal line.

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U.S. Department of Commerce, Patent and Trademark Office		Docket No.	Serial No.
(PTO Form 1449 modified)		AMAT/6437/ETCH/METAL/JB1	10/092,456
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant Hwang, et al.	Confirmation No. 1212
(Use several sheets if necessary)		Filing Date	Group
	Examiner Dung Anh Le	March 6, 2002	2818

**U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A1						
	A2						
	A3						
	A4						
	A5						

Foreign Patent Documents

*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
	B1						<input type="checkbox"/>	<input type="checkbox"/>
	B2						<input type="checkbox"/>	<input type="checkbox"/>
	B3						<input type="checkbox"/>	<input type="checkbox"/>
	B4						<input type="checkbox"/>	<input type="checkbox"/>
	B5						<input type="checkbox"/>	<input type="checkbox"/>

OTHER ART

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	Jung, K.B., et al., "Long term stability of dry etched magnetoresistive random access memory elements", <i>Journal of Vacuum Science and Technology: Part A</i> ; American Institute of Physics, New York, U.S., Vol. 18, No. 1, January 2000 (2000-01), pp. 268-272, XP001145970, ISSN: 0734-2101.
	C2	van Delft, F.C.M.J.M., et al., "The etch mechanisms of magnetic materials in an HCl plasma", Fusion Technology and Plasmas Session of the Twelfth International Vacuum Congress (IVC-12) and Eighth International Conference on Solid Surfaces (ICSS-8), The Hague, Netherlands, 12-16 Oct. 1992, Vol. 200, No. 3, pp. 366-370, XP008022404, <i>Journal of Nuclear Materials</i> , May 1993, Netherlands, ISSN: 0022-3115.
	C3	Cho, H. et al., "Inductively coupled plasma etching of CoFeB, CoZr, CoSm and FeMn thin films in interhalogen mixtures", <i>Materials Science and Engineering B (Solid-State Materials for Advanced Technology)</i> , 15 June 1999, Elsevier, Switzerland, Vol. B60, No. 2, pp. 107-111, XP004175032, ISSN: 0921-5107.

Examiner	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.